

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
-30V	6.8mΩ @ V <sub>GS</sub> = -10V	-50A
	13mΩ @ V <sub>GS</sub> = -4.5V	-36A

## Description and Applications

This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

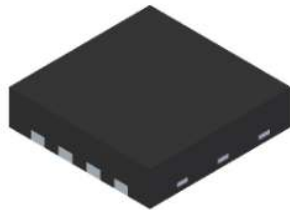
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

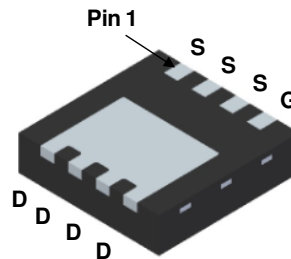
- Low R<sub>DS(ON)</sub> – Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (Test in Production)– Ensures More Reliability
- HBM ESD Protection Level of 8kV Typical
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

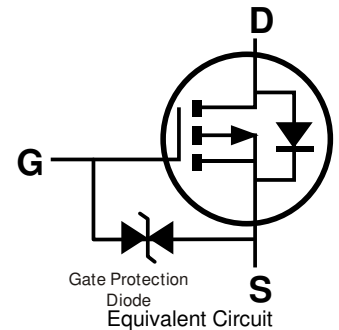
- Case: V-DFN3333-8 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Below Diagram  
Terminals: Finish –NiPdAu over Copper Leadframe.  
Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.030 grams (Approximate)



Top View



Bottom View

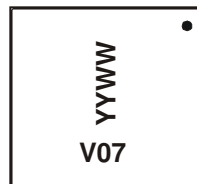


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3007SCGQ-7	V-DFN3333-8 (Type B)	2,000/Tape & Reel
DMP3007SCGQ-13	V-DFN3333-8 (Type B)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
  5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



V07= Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 18 = 2018)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-30	V
Gate-Source Voltage	V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 8) V <sub>GS</sub> = -10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	-50
Steady State		T <sub>C</sub> = +70°C	-40
Maximum Continuous Body Diode Forward Current (Note 8)	I <sub>S</sub>	-40	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-100	A
Avalanche Current (Note 9) L = 1mH	I <sub>AS</sub>	-16	A
Avalanche Energy (Note 9) L = 1mH	E <sub>AS</sub>	130	mJ

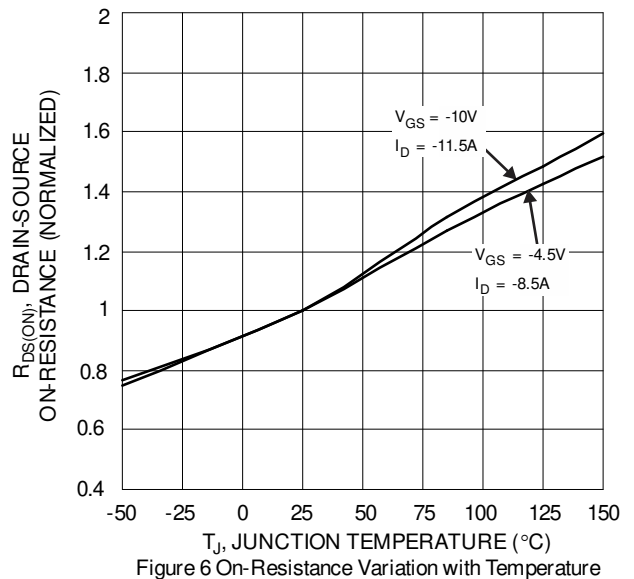
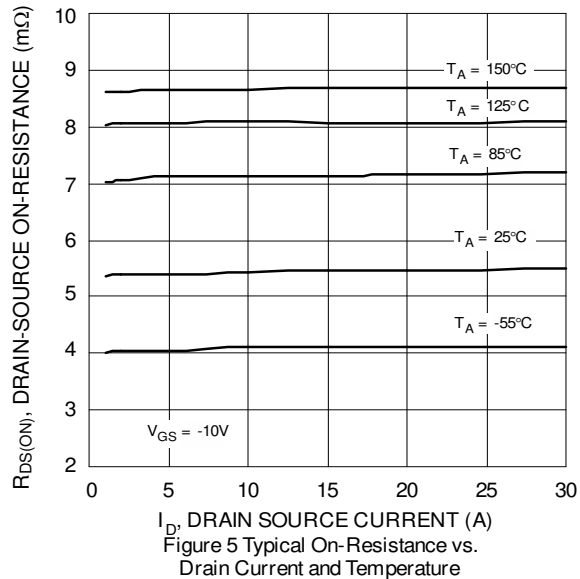
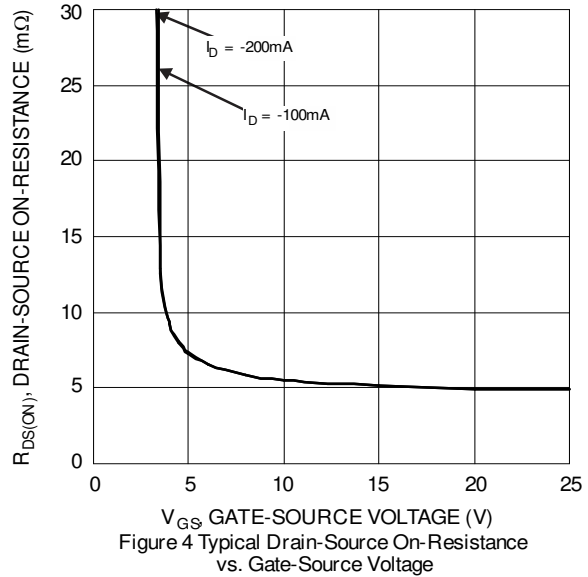
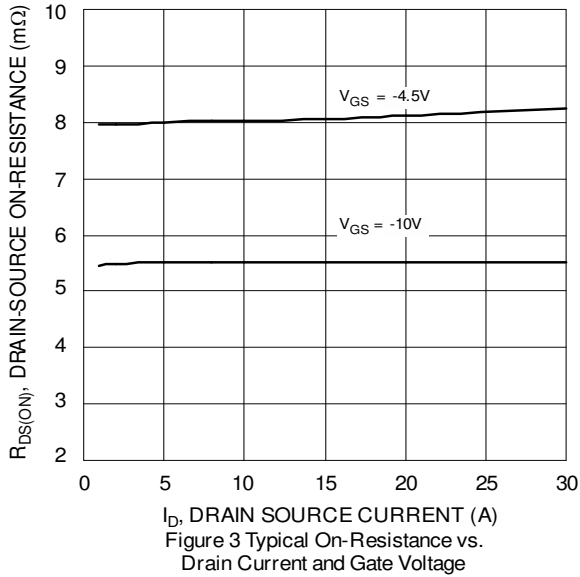
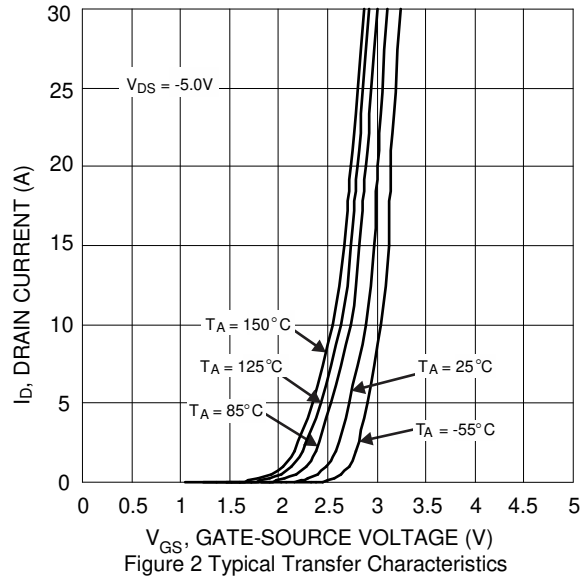
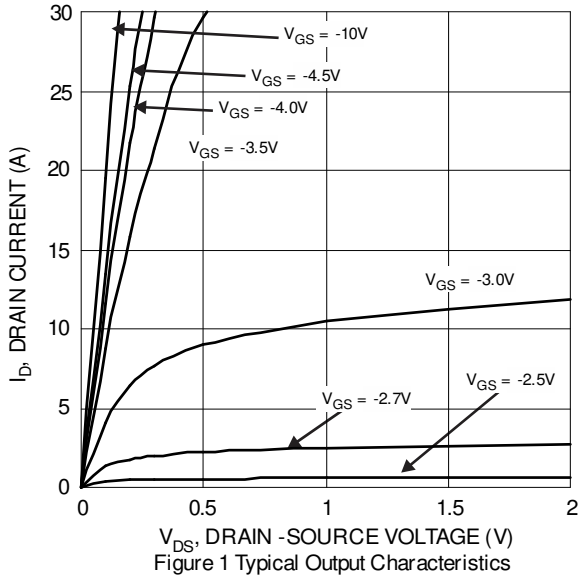
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.0	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	124	°C/W
Total Power Dissipation (Note 7)	P <sub>D</sub>	2.4	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	52	°C/W
Thermal Resistance, Junction to Case (Note 8)	R <sub>θJC</sub>	4.0	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 10)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 10)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	—	-3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>D(S)ON</sub>	—	5.7	6.8	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -11.5A
		—	8.0	13		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -8.5A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 11)</b>						
Input Capacitance	C <sub>iss</sub>	—	2,826	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	606	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	305	—	pF	
Gate Resistance	R <sub>g</sub>	—	23	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	31.2	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -11.5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	64.2	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	10.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	11.6	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.8	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>g</sub> = 6Ω, I <sub>D</sub> = -11.5A
Turn-On Rise Time	t <sub>R</sub>	—	4.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	306	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	125	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	19	—	ns	I <sub>S</sub> = -11.5A, dI/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



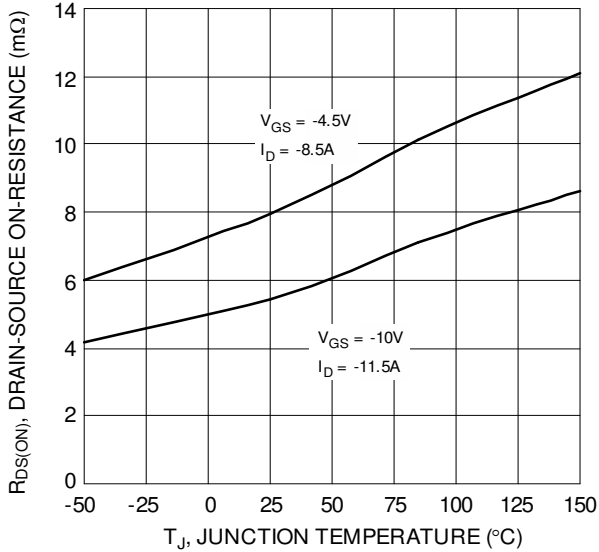


Figure 7 On-Resistance Variation with Temperature

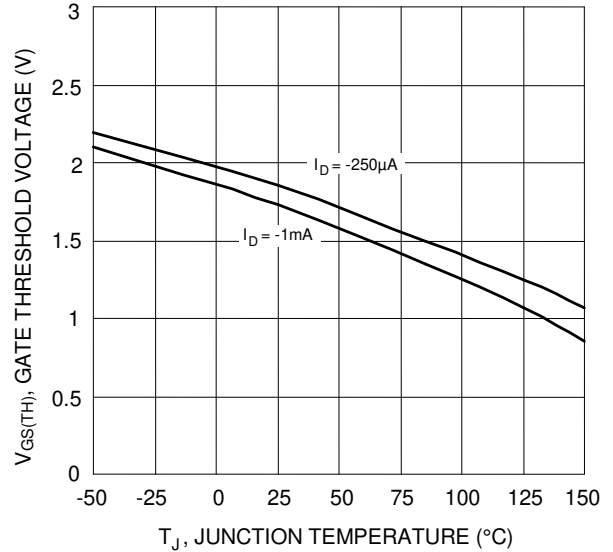


Figure 8 Gate Threshold Variation vs. Junction Temperature

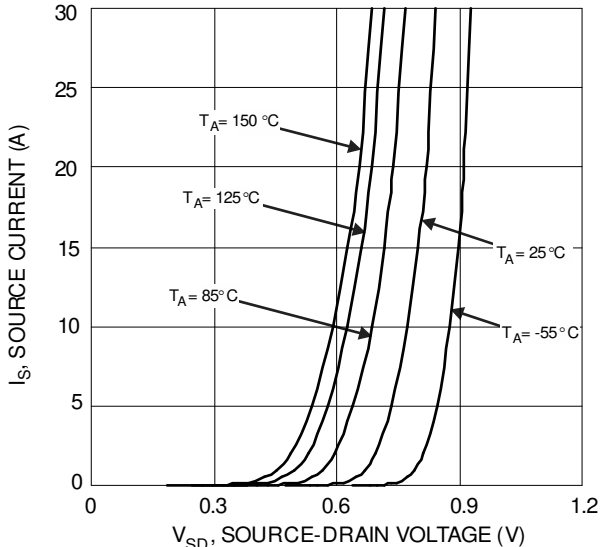


Figure 9 Diode Forward Voltage vs. Current

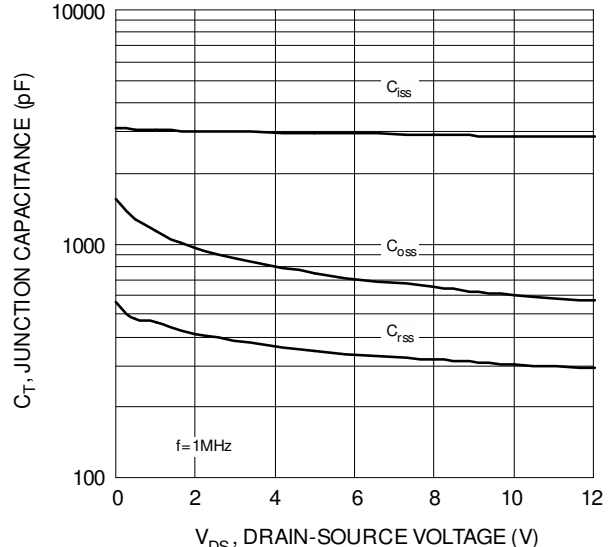


Figure 10 Typical Junction Capacitance

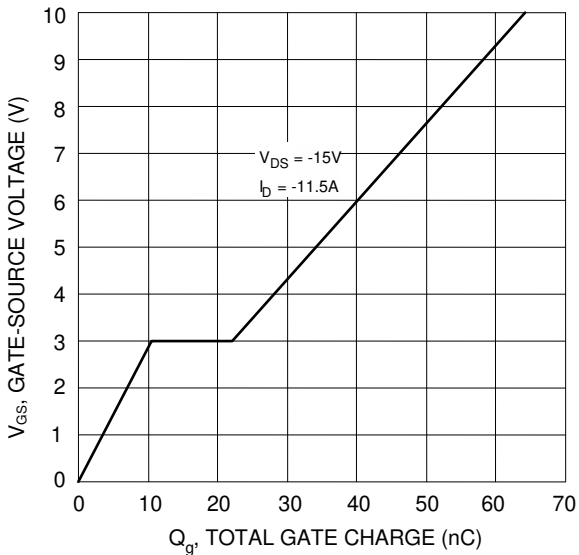


Figure 11 Gate Charge

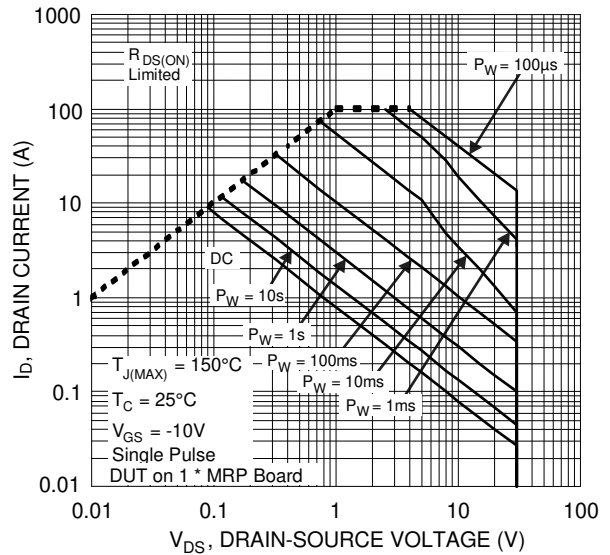
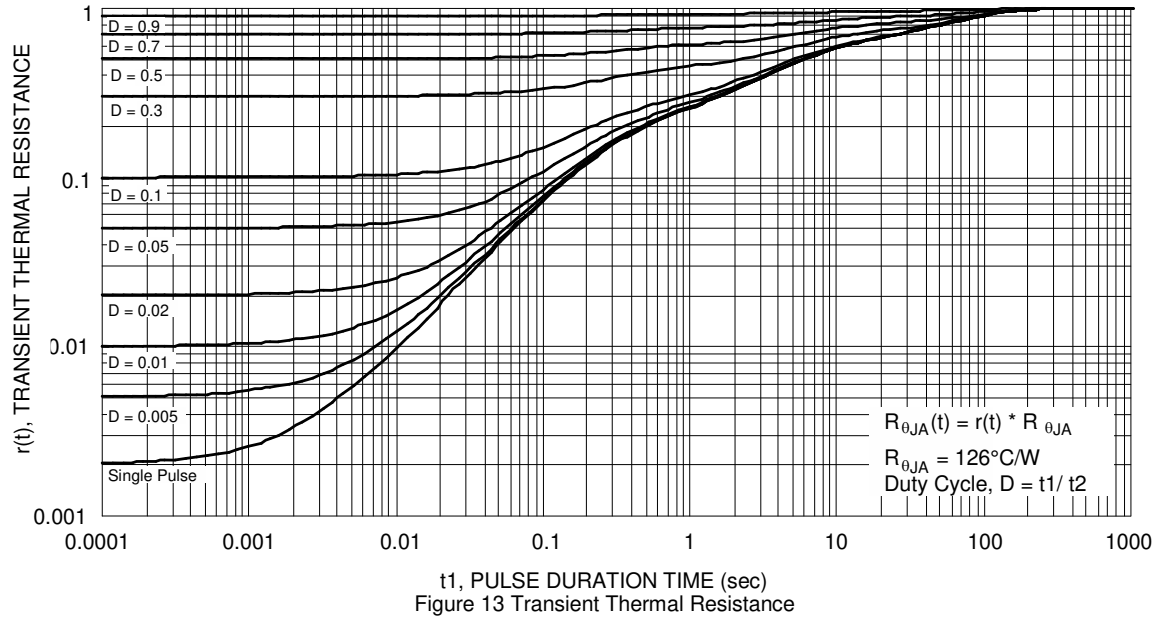


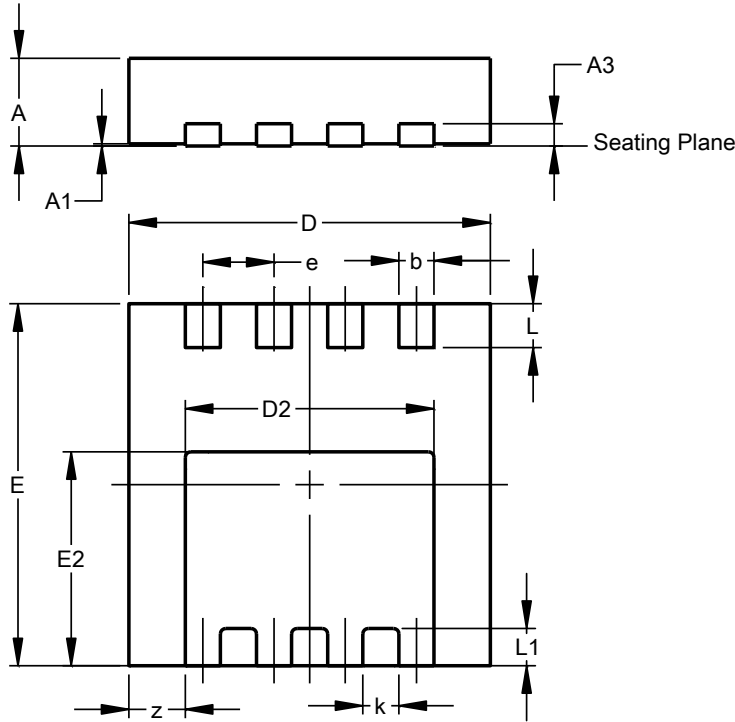
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN3333-8 (Type B)

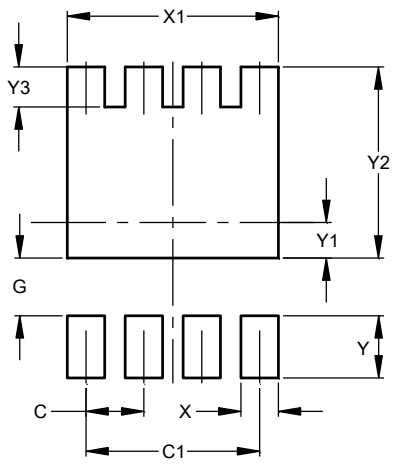


V-DFN3333-8 (Type B)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.27	0.37	0.32
D	3.25	3.35	3.30
D2	2.17	2.37	2.27
E	3.25	3.35	3.30
E2	1.85	2.05	1.95
e	--	--	0.65
k	--	--	0.33
L	0.35	0.45	0.40
L1	--	--	0.34
z	--	--	0.515
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN3333-8 (Type B)



Dimensions	Value (in mm)
C	0.650
C1	1.950
G	0.650
X	0.420
X1	2.370
Y	0.700
Y1	0.400
Y2	2.150
Y3	0.450

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